

N-Ch 30V Fast Switching MOSFETs
Description

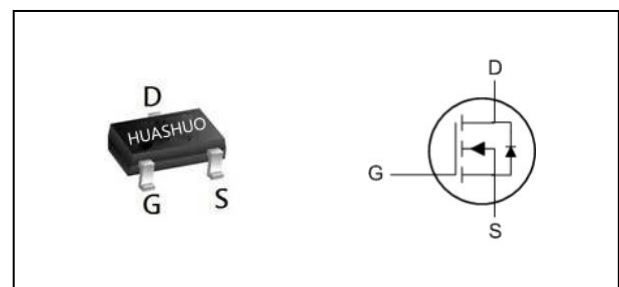
The HSS3008 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The HSS3008 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	30	V
$R_{DS(ON),typ}$	12	m Ω
I_D	8	A

SOT-23L Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6.3	A
I_{DM}	Pulsed Drain Current ²	32	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ³	1.4	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	100	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	62	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.023	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =8A	---	12	15	mΩ
		V _{GS} =4.5V, I _D =6A	---	16	20	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	1.6	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =30V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.6	---	Ω
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _D =8A	---	23	---	nC
Q _{gs}	Gate-Source Charge		---	1.4	---	
Q _{gd}	Gate-Drain Charge		---	2.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =1.5Ω I _D =8A	---	5	---	ns
T _r	Rise Time		---	9	---	
T _{d(off)}	Turn-Off Delay Time		---	32	---	
T _f	Fall Time		---	6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	851	---	pF
C _{oss}	Output Capacitance		---	98	---	
C _{rss}	Reverse Transfer Capacitance		---	74	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	8	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	32	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Characteristics

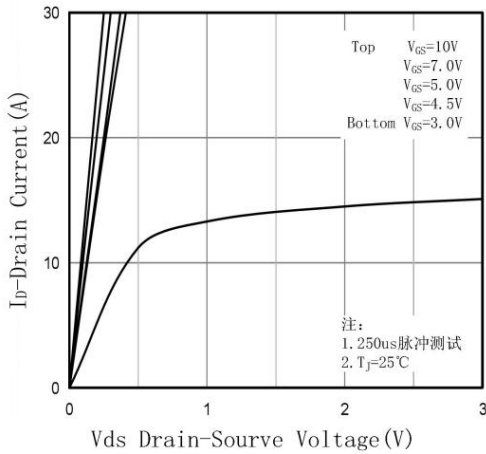


Fig.1 Output Characteristic

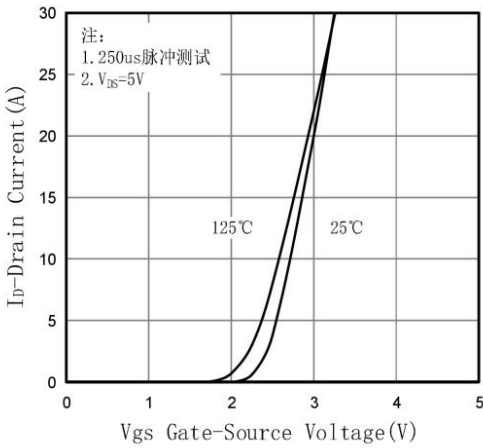


Fig.3 Transfer Characteristic

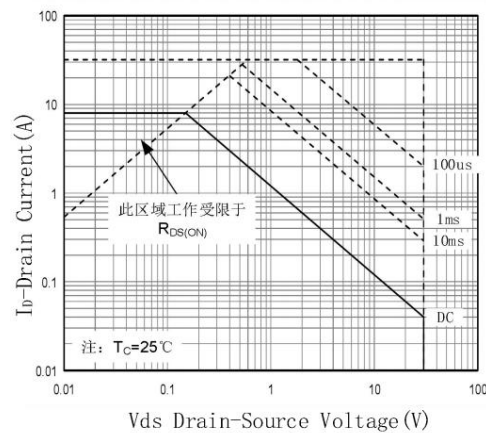


Fig.5 Safe Operation Area

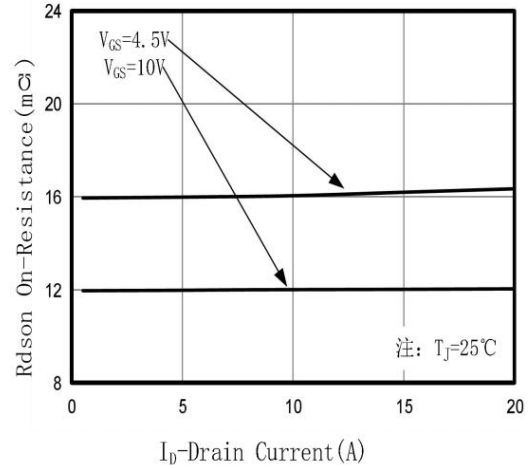


Fig.2 On-Resistance vs. Drain Current

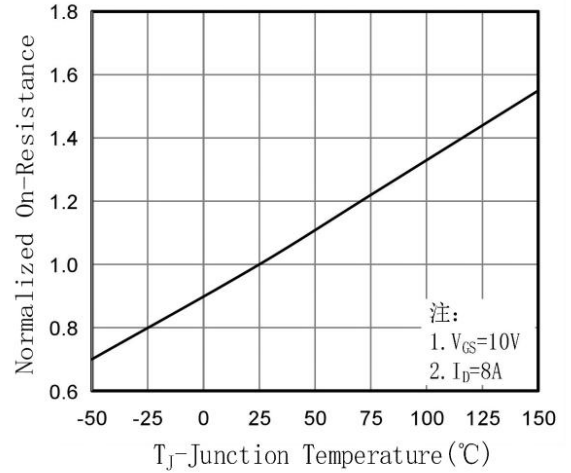


Fig.4 On-Resistance vs. Junction Temperature

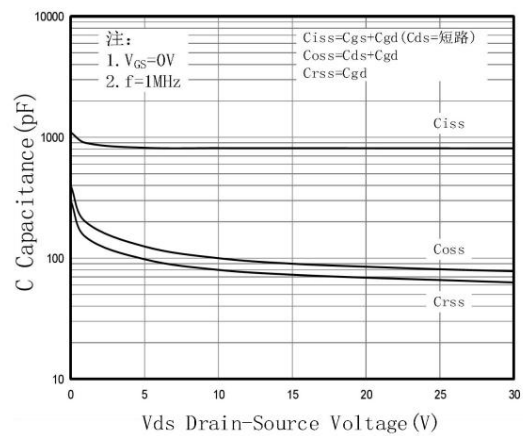


Fig.6 Capacitance Characteristic



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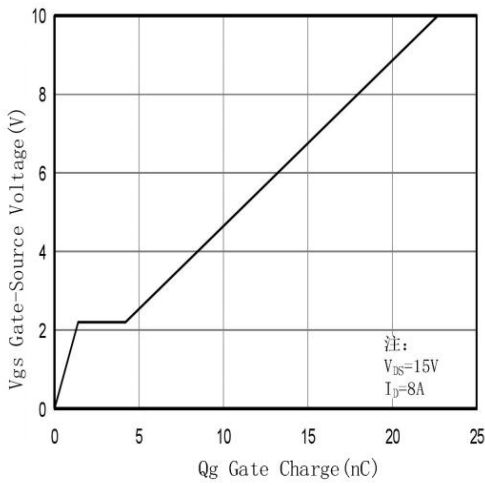


Fig.7 Gate-Charge Characteristic

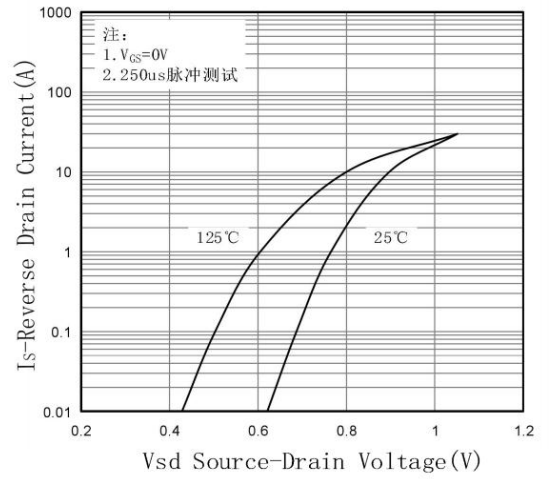


Fig.8 Body Diode Characteristic

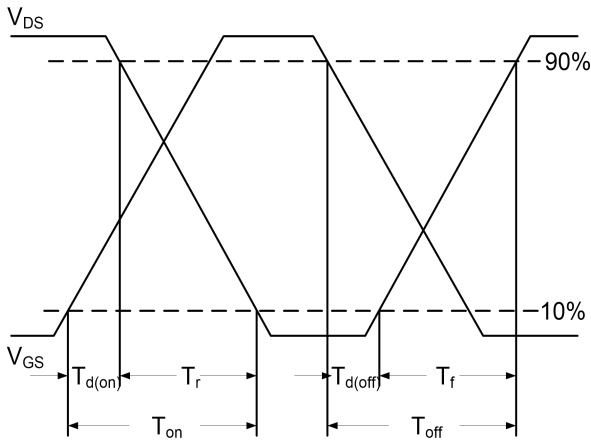


Fig.9 Switching Time Waveform

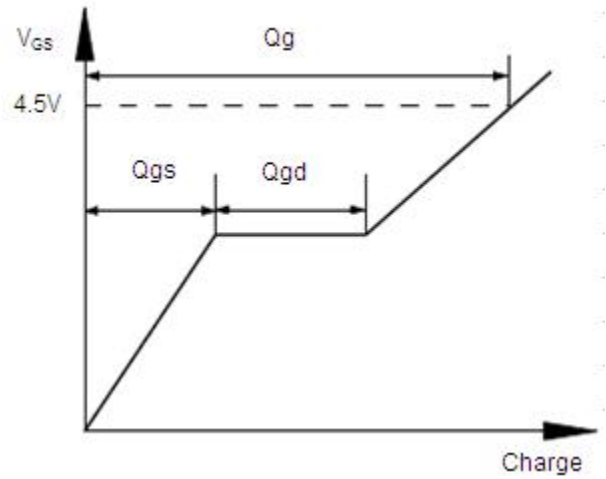
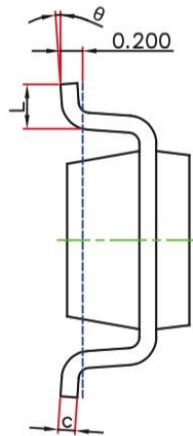
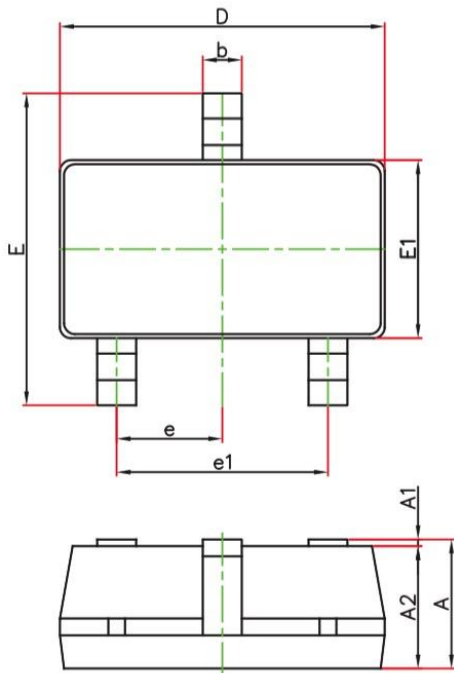


Fig.10 Gate Charge Waveform



Ordering Information

Part Number	Package code	Packaging
HSS3008	SOT-23L	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°